

# CMD25N10L/CMU25N10L

100V, 53mΩ typ., 25A N-Channel MOSFET

## General Description

The 25N10L uses advanced trench technology to provide excellent RDS(ON) . This device is suitable for use as a wide variety of applications.

## Features

- Low On-Resistance
- 100% avalanche tested
- RoHS Compliant

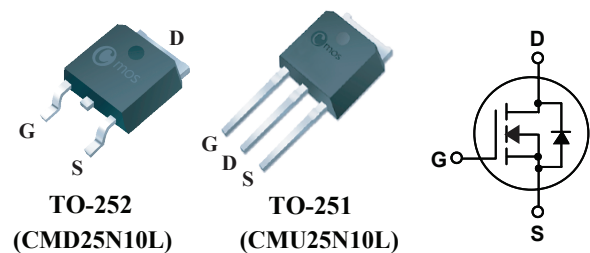
## Product Summary

BVDSS	RDS(on) max.	ID
100V	62mΩ	25A

## Applications

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

## TO-252/251 Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	100	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current	25	A
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current	17	A
I <sub>DM</sub>	Pulsed Drain Current	100	A
EAS	Single Pulse Avalanche Energy <sup>1</sup>	32	mJ
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation	60	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-ambient	---	75	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-case	---	2.08	°C/W

### Electrical Characteristics(T<sub>J</sub>=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	100	---	---	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =10A	---	53	62	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	---	54	70	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.0	---	2.0	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V	---	---	1	μA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =5A	---	15	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	2.2	---	Ω
Q <sub>g</sub>	Total Gate Charge	I <sub>D</sub> =20A V <sub>DS</sub> =50V V <sub>GS</sub> =10V (Note 2)	---	55	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	9	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	13	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DS</sub> =50V	---	20	---	ns
T <sub>r</sub>	Rise Time	V <sub>GS</sub> =10V	---	30	---	
T <sub>d(off)</sub>	Turn-Off Delay Time	R <sub>G</sub> =50Ω, R <sub>L</sub> =5Ω	---	185	---	
T <sub>f</sub>	Fall Time	I <sub>D</sub> =10A (Note 2)	---	60	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz	---	2900	---	pF
C <sub>oss</sub>	Output Capacitance		---	60	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	50	---	

### Diode Characteristics

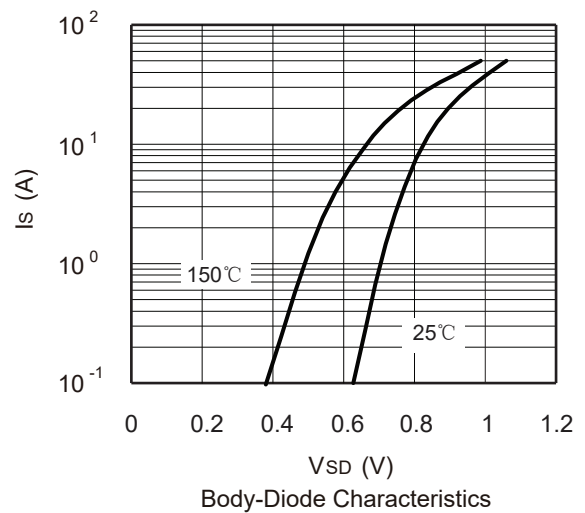
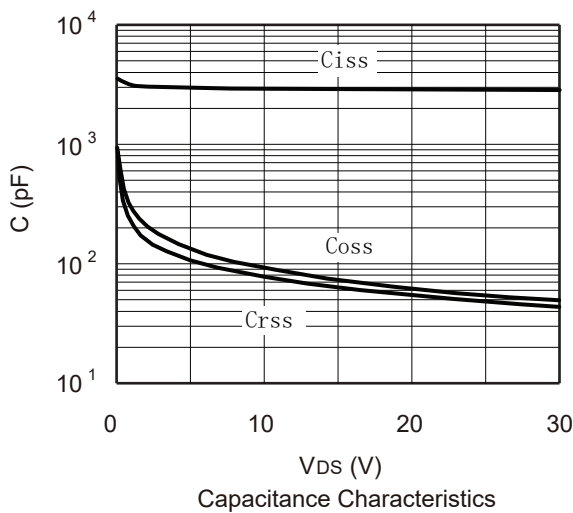
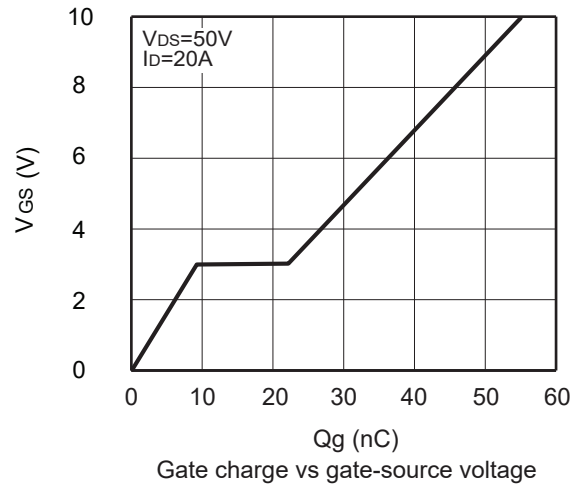
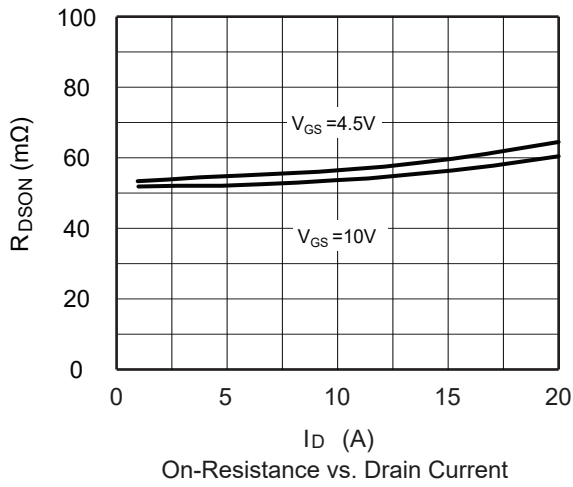
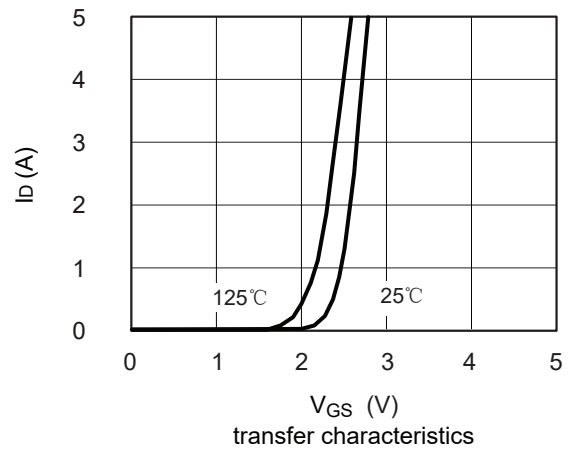
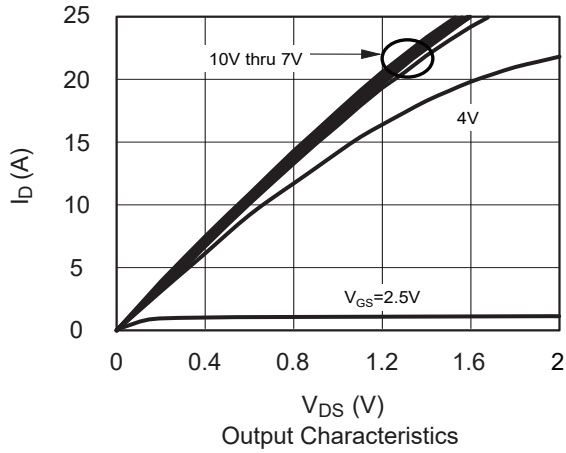
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	25	A
I <sub>SM</sub>	Pulsed Source Current		---	---	100	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =10A, T <sub>J</sub> =25°C	---	0.82	1.2	V

Note :

- 1.The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=50V, V<sub>GS</sub>=10V, L=0.5mH, I<sub>D</sub>=16.5A.
- 2.Guaranteed by design, not subject to production testing.

This product has been designed and qualified for the consumer market.  
Cmos assumes no liability for customers' product design or applications.  
Cmos reserves the right to improve product design, functions and reliability without notice. Please refer to the latest version of specification.

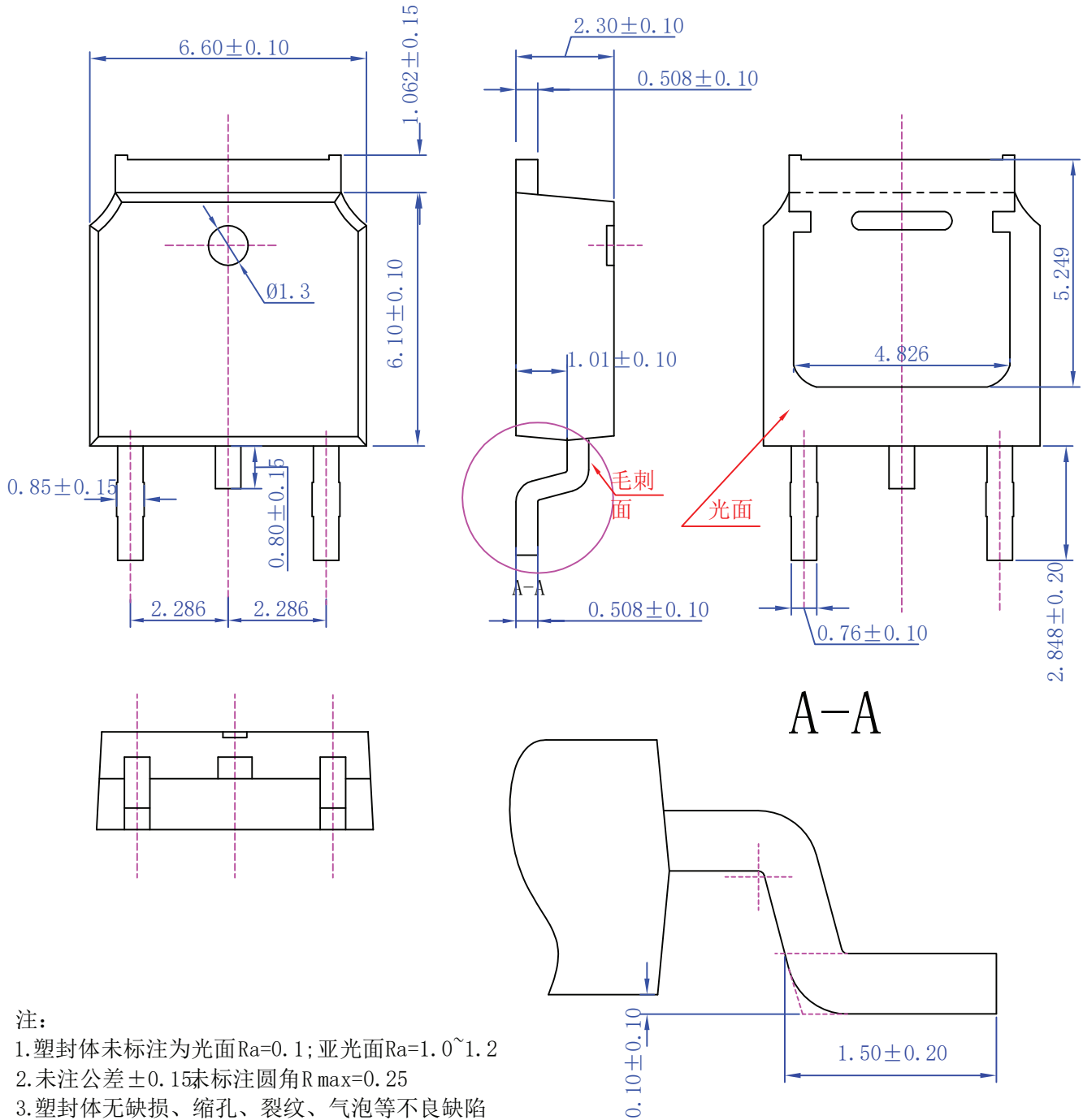
Typical Characteristics



Package Dimension

TO-252

Unit :mm



注:

1. 塑封体未标注为光面Ra=0.1; 亚光面Ra=1.0~1.2
2. 未注公差±0.15未标注圆角R max=0.25
3. 塑封体无缺损、缩孔、裂纹、气泡等不良缺陷
4. 标注单位mm
5. 顶针孔不允许凸出塑封体表面

Package Dimension

TO-251A

Unit :mm

